

ABSTRACT OF THE DISCLOSURE

A TFT is provided completely separated by an insulating film, in which a parasitic MOSFET is not generated at ends of a semiconductor layer, and the variation in characteristics is small. At least one portion of the ends in the gate-width direction of a gate electrode forming the TFT is disposed in a semiconductor region which forms the TFT, and the ends in the gate-length direction of the gate electrode extend toward the outside of the semiconductor region forming the TFT. With this arrangement, a uniform TFT in which a parasitic MOSFET is not generated at the ends in the gate-width direction is obtainable.